CPH3325

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−100	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		−0.3	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−1.2	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D= −1mA, V_{GS}=0	−100			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}= −100V, V_{GS}=0			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}= ±16V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}= −10V, I_D= −1mA	−1.2		−2.6	V
Forward Transfer Admittance	|yfs|	V_{DS}= −10V, I_D= −150mA	0.2	0.45		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D= −150mA, V_{GS}= −10V		3.0	3.9	Ω
	R_{DS}(on)2	I_D= −150mA, V_{GS}= −4V		3.6	5.0	Ω
Input Capacitance	Ciss	V_{DS}= −20V, f=1MHz		78		pF
Output Capacitance	Coss	V_{DS}= −20V, f=1MHz		6.0		pF
Reverse Transfer Capacitance	Crss	V_{DS}= −20V, f=1MHz		4.0		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		6		ns
Rise Time	t_r	See specified Test Circuit.		3		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		16		ns
Fall Time	t_f	See specified Test Circuit.		16		ns

Marking : YA